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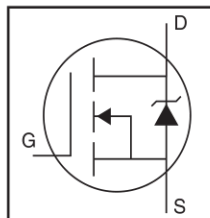
HEXFET® Power MOSFET

Applications

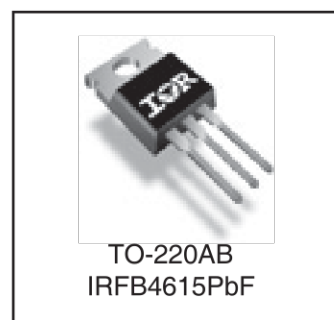
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free



V_{DSS}		150V
$R_{DS(on)}$	typ.	32mΩ
	max.	39mΩ
I_D		35A



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	35	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	25	
I_{DM}	Pulsed Drain Current ①	140	
P_D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	144	W
	Linear Derating Factor	0.96	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery ③	38	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

Avalanche Characteristics

E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	109	mJ
I_{AR}	Avalanche Current ①	See Fig. 14, 15, 22a, 22b,	A
E_{AR}	Repetitive Avalanche Energy ④		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑤	—	1.045	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50		
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑦⑧	—	62	

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.19	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 5mA$ ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	32	39	m Ω	$V_{GS} = 10V, I_D = 21A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 100\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 150V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 150V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
$R_{G(int)}$	Internal Gate Resistance	—	2.7	—	Ω	

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	35	—	—	S	$V_{DS} = 50V, I_D = 21A$
Q_g	Total Gate Charge	—	26	—	nC	$I_D = 21A$
Q_{gs}	Gate-to-Source Charge	—	8.6	—		$V_{DS} = 75V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	9.0	—		$V_{GS} = 10V$ ④
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	17	—		$I_D = 21A, V_{DS} = 0V, V_{GS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	15	—	ns	$V_{DD} = 98V$
t_r	Rise Time	—	35	—		$I_D = 21A$
$t_{d(off)}$	Turn-Off Delay Time	—	25	—		$R_G = 7.3\Omega$
t_f	Fall Time	—	20	—		$V_{GS} = 10V$ ④
C_{iss}	Input Capacitance	—	1750	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	155	—		$V_{DS} = 50V$
C_{rss}	Reverse Transfer Capacitance	—	40	—		$f = 1.0MHz$ (See Fig.5)
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related)⑥	—	179	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 120V$ ⑦ (See Fig.11)
$C_{oss \text{ eff. (TR)}}$	Effective Output Capacitance (Time Related)⑤	—	382	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 120V$ ⑤

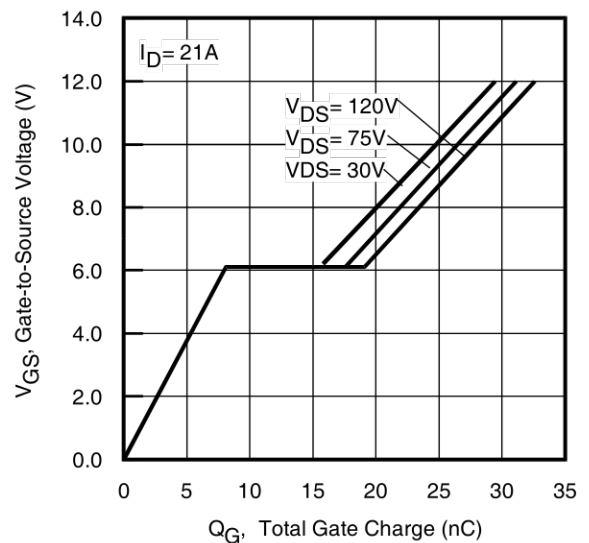
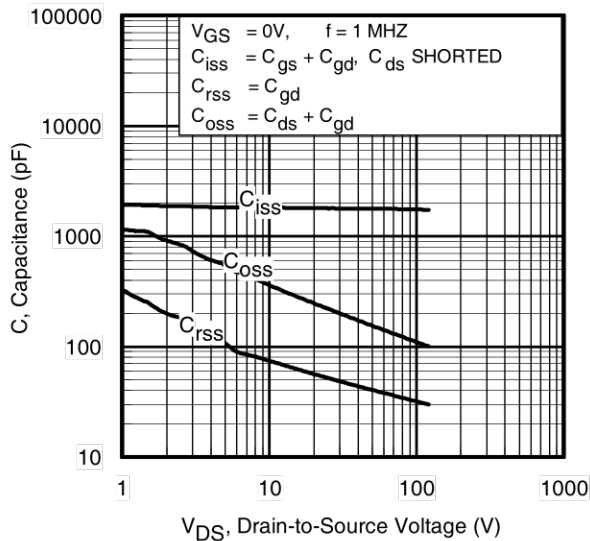
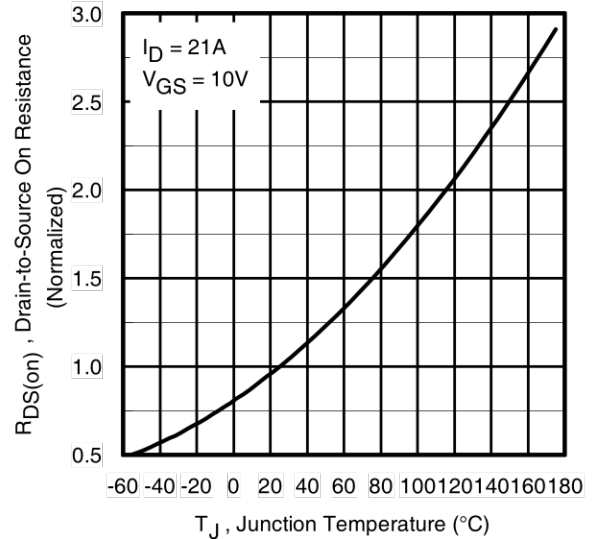
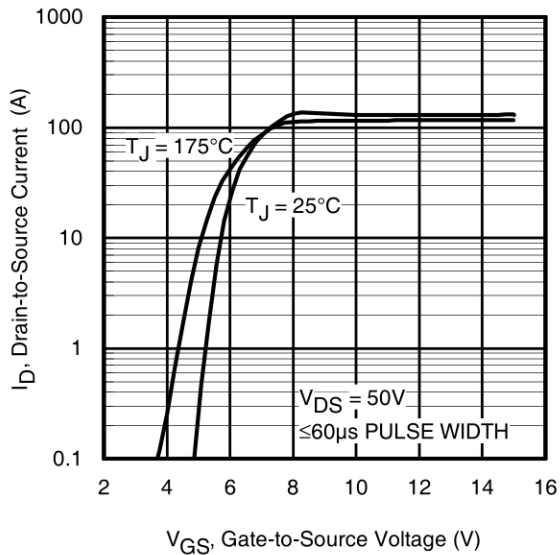
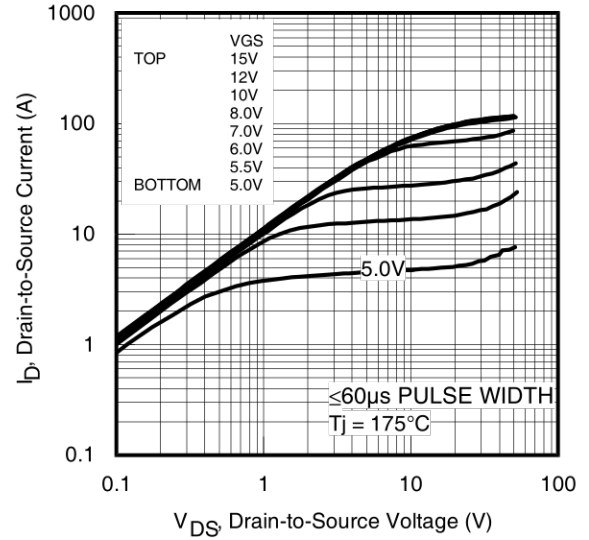
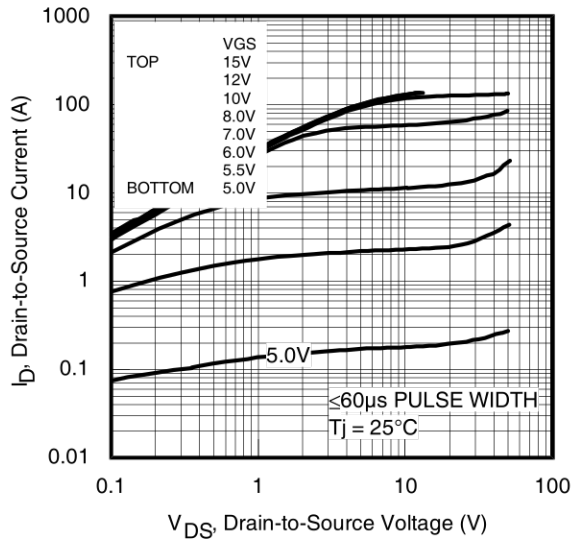
Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	35	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	140		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 21A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	70	—	ns	$T_J = 25^\circ\text{C}$ $V_R = 100V,$
		—	83	—		$T_J = 125^\circ\text{C}$ $I_F = 21A$
Q_{rr}	Reverse Recovery Charge	—	177	—	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100A/\mu s$ ④
		—	247	—		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	4.9	—	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
 ② Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.51mH$
 $R_G = 25\Omega, I_{AS} = 21A, V_{GS} = 10V$. Part not recommended for use above this value.
 ③ $I_{SD} \leq 21A, di/dt \leq 549A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$.
 ④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.

- ⑤ $C_{oss \text{ eff. (TR)}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
 ⑥ $C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
 ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994
 ⑧ R_θ is measured at T_J approximately 90°C



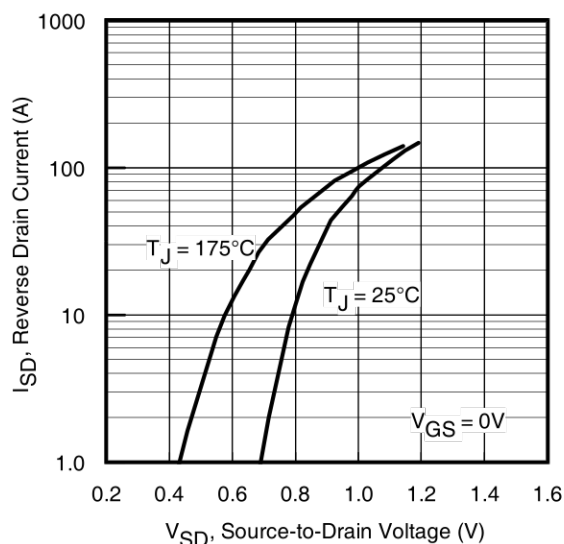


Fig 7. Typical Source-Drain Diode Forward Voltage

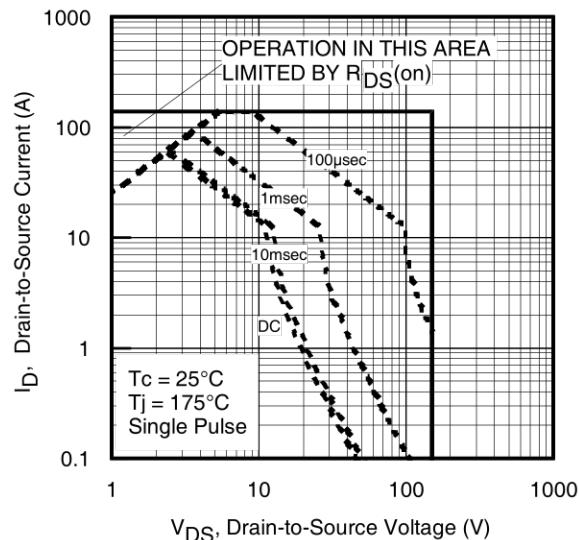


Fig 8. Maximum Safe Operating Area

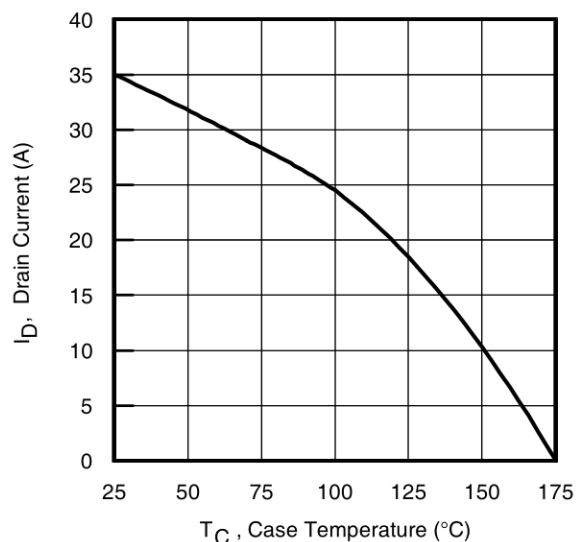


Fig 9. Maximum Drain Current vs. Case Temperature

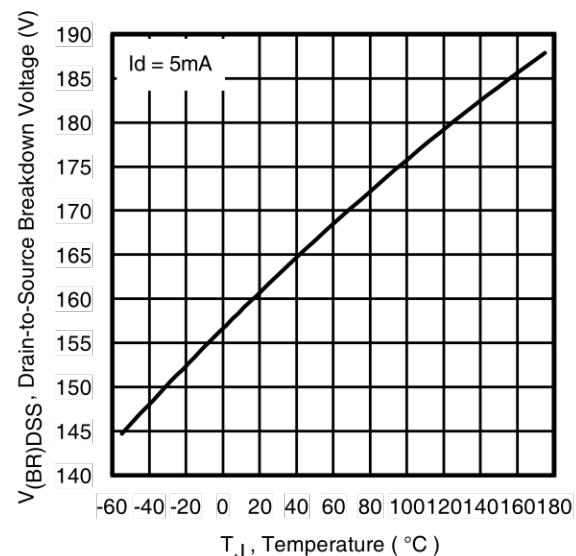


Fig 10. Drain-to-Source Breakdown Voltage

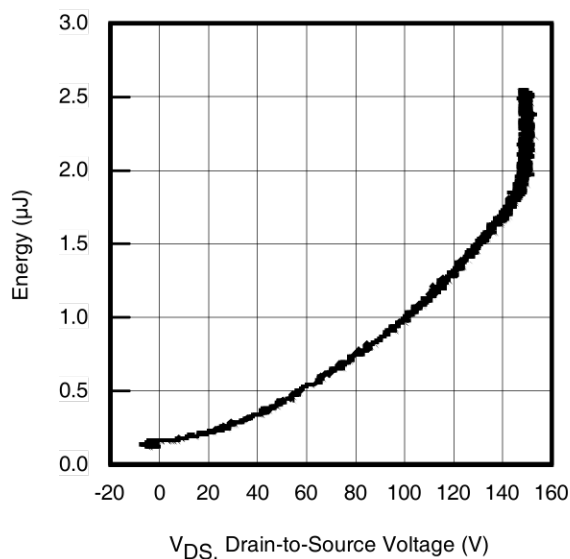


Fig 11. Typical C_{OSS} Stored Energy

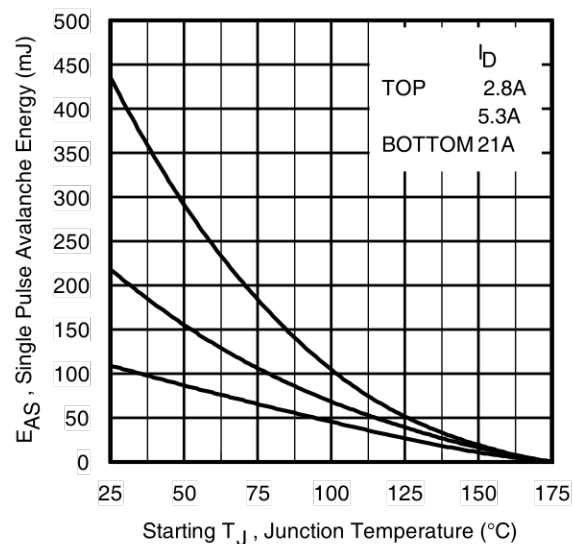


Fig 12. Maximum Avalanche Energy vs. Drain Current

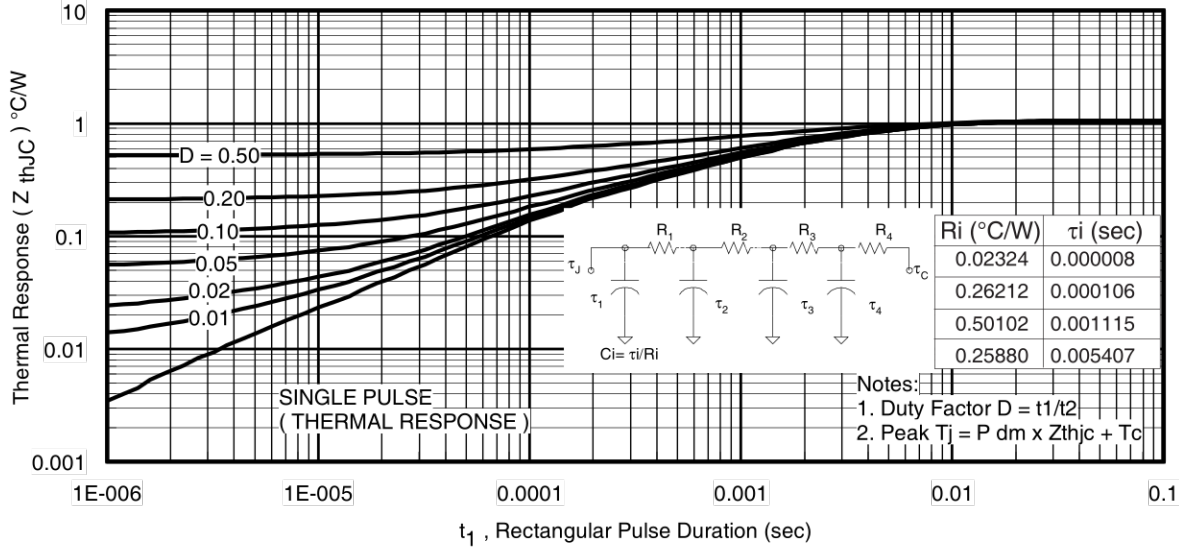


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

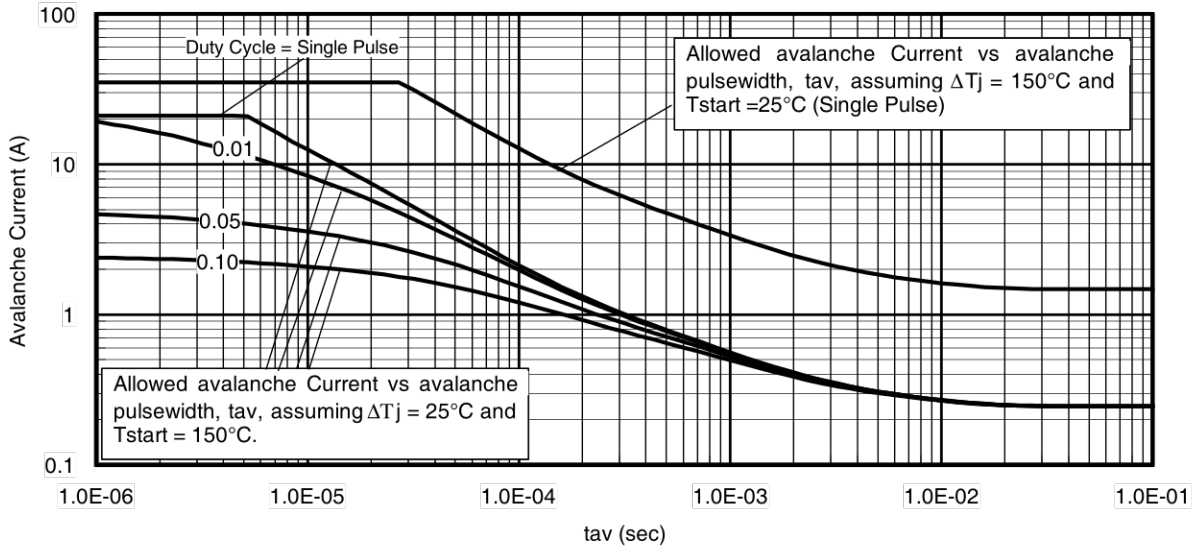


Fig 14. Typical Avalanche Current vs. Pulsewidth

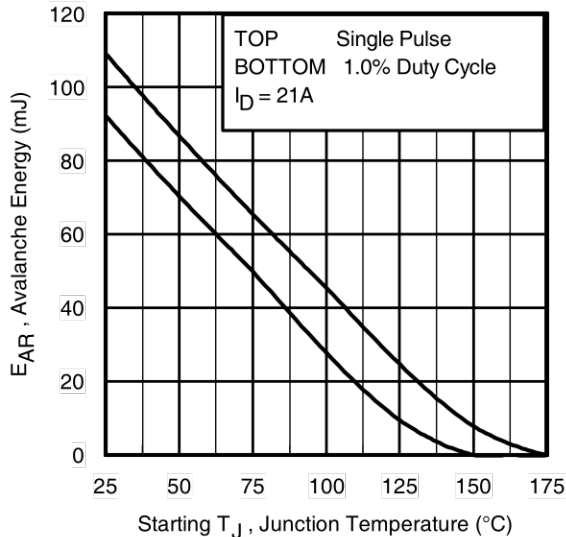


Fig 15. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_D (ave)$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_D (ave) = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2 \Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS} (AR) = P_D (ave) \cdot t_{av}$$

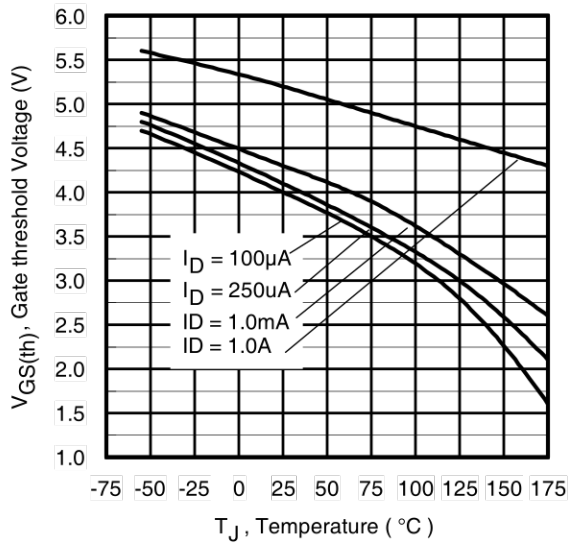


Fig. 16. Threshold Voltage vs. Temperature

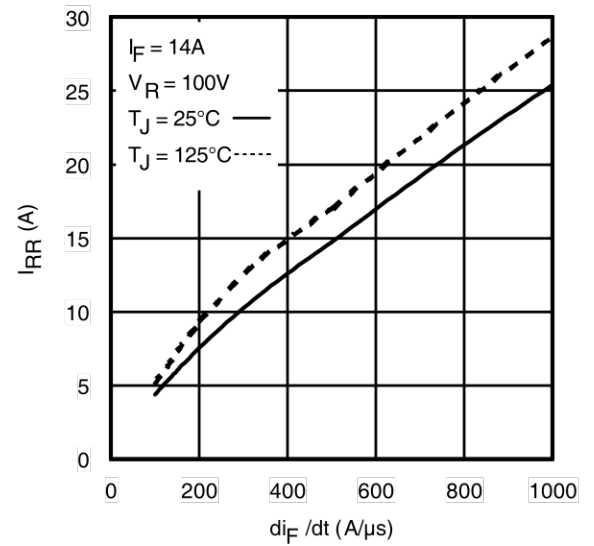


Fig. 17 - Typical Recovery Current vs. di_F/dt

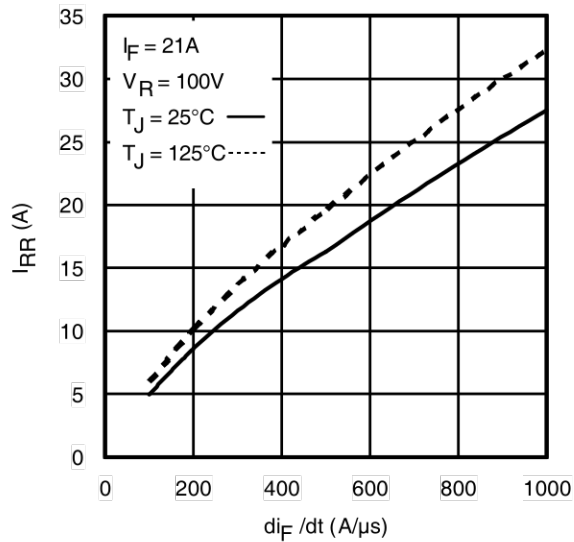


Fig. 18 - Typical Recovery Current vs. di_F/dt

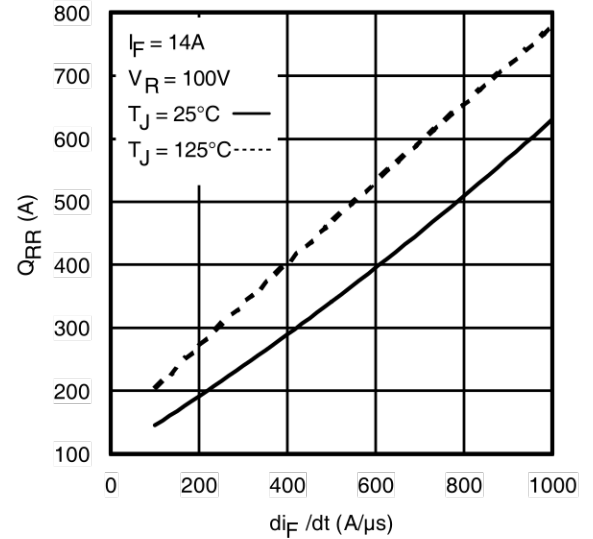


Fig. 19 - Typical Stored Charge vs. di_F/dt

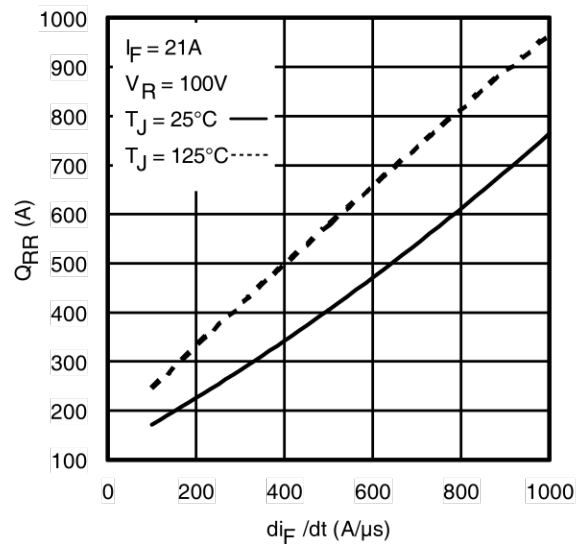


Fig. 20 - Typical Stored Charge vs. di_F/dt

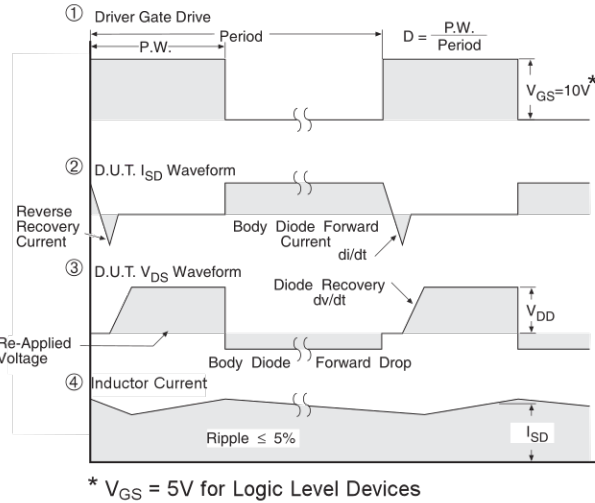
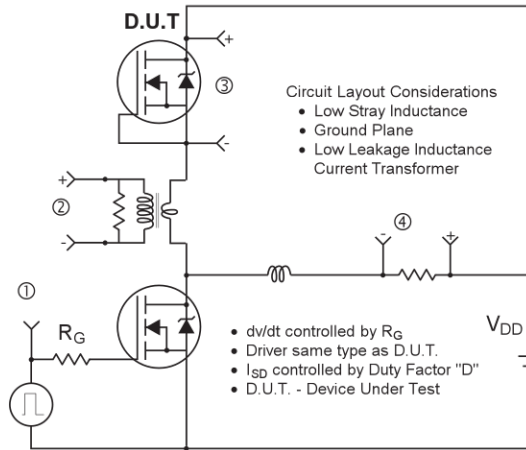


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

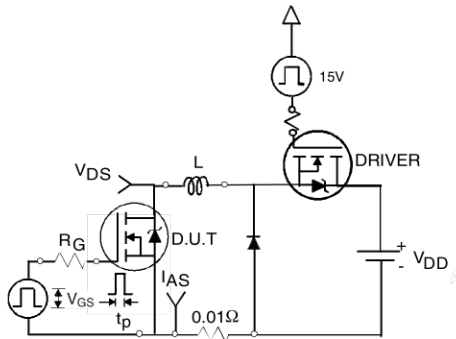


Fig 22a. Unclamped Inductive Test Circuit

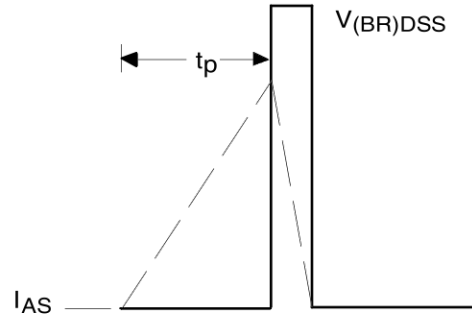


Fig 22b. Unclamped Inductive Waveforms

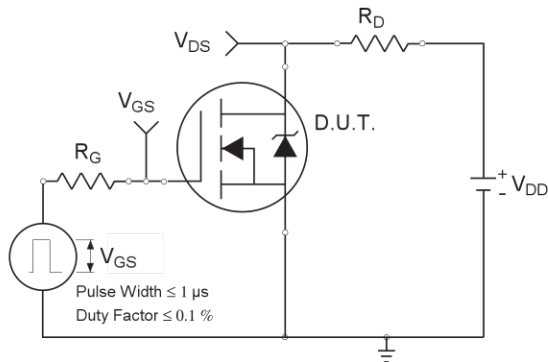


Fig 23a. Switching Time Test Circuit

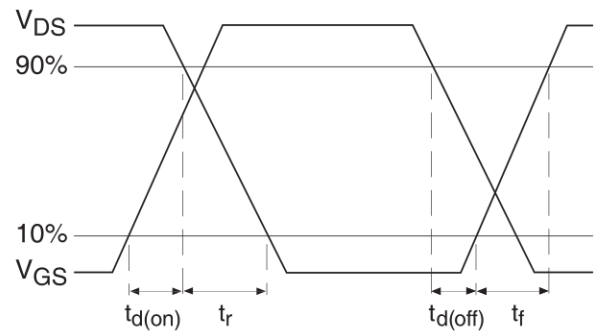


Fig 23b. Switching Time Waveforms

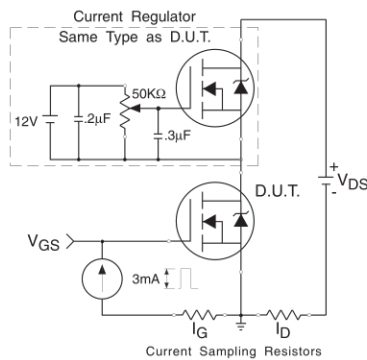


Fig 24a. Gate Charge Test Circuit

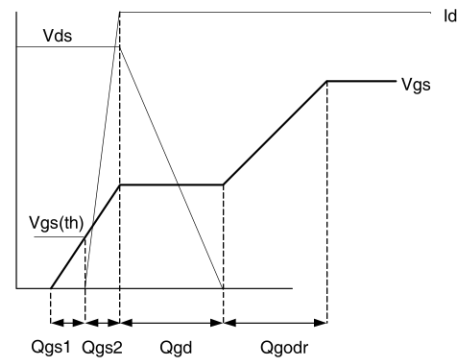
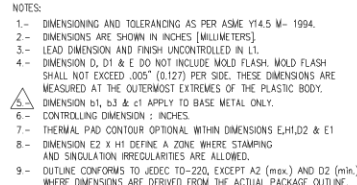


Fig 24b. Gate Charge Waveform

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTE
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.51	.014	.024	
c1	0.36	0.66	.014	.022	5
D	14.22	16.51	.560	.650	
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	
E	9.65	10.67	.380	.420	4, 7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC	100 BSC			
e1	5.08 BSC	200 BSC			
h1	5.84	6.86	.230	.270	7, 8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

1.- ANODE
2.- CATHODE

8

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